

WAFER PROCESSING METHOD

ABSTRACT OF THE DISCLOSURE

A wafer processing method includes: a cut groove forming step of cutting a device layer stacked on a semiconductor substrate along each of the division lines to form a cut groove; a modified layer forming step of positioning a focal point of a laser beam having a transmission wavelength to the semiconductor substrate inside an area of the semiconductor substrate corresponding to a predetermined one of the division lines and applying the laser beam to the wafer from a back surface of the wafer, thereby forming a plurality of modified layers inside the wafer along all of the division lines; and a dividing step of grinding the back surface of the wafer to be thinned, and causing a crack to grow from each of the modified layers formed inside the area of the semiconductor substrate corresponding to the predetermined one of the division lines to the front surface side of the wafer, thereby dividing the wafer into individual device chips.

FIGURE 6B